



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

9/A
2-402
R. Stiles

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TECHNOLOGY CENTER 2800

In re Application of

Makoto SASAKI

Serial No.: 09/532,892 ✓

Group Art Unit: 2815

Filed: March 22, 2000

Examiner: P. Brock, II

For: SEMICONDUCTOR DEVICE WITH COPPER FUSE SECTION

Honorable Assistant Commissioner of Patents
Washington, D.C. 20231

AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated November 1, 2001, please amend the above-identified application as follows:

IN THE SPECIFICATION:

Please amend the paragraph from page 7, line 19 to page 10, line 10 as follows:

As shown in Fig. 1, a low dielectric constant film 3 is formed on a silicon substrate 1 in the DRAM. The low dielectric constant film 3 is composed of film sections 3-1, 3-2 and 3-3 which are laminated in order. A wiring line structure 2 is formed in the low dielectric constant insulating film 3. The wiring line structure 2 is composed of wiring lines 4 and 5, wiring lines (e.g., conductive plugs) 12 and 13 and a fuse section 11. The wiring lines 4 and 5 are formed on the film section 3-2 of the low dielectric film 3. The fuse section 11 is formed on the film section 3-1 of the low dielectric film 3. As shown in Figs. 1 and 2, the low dielectric constant film 3 is covered by a passivation film 7 in the area between the wiring lines 4 and 5. A laser opening 8 is formed to the fuse section 11 through the passivation film 7 and the low dielectric constant insulating film 3 in the area between the wiring lines 4 and

5.